
2SC4913

Silicon NPN Triple Diffused

HITACHI

Application

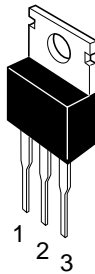
High voltage amplifier

Features

- High breakdown voltage
- $V_{(BR)CEO} = 2000 \text{ V min}$

Outline

TO-220AB



1. Base
2. Collector (Flange)
3. Emitter

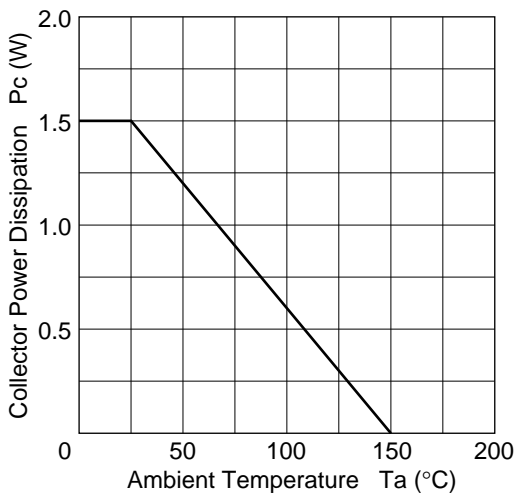
Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Ratings	Unit
Collector to base voltage	V_{CBO}	2000	V
Collector to emitter voltage	V_{CEO}	2000	V
Emitter to base voltage	V_{EBO}	6	V
Collector current	I_C	20	mA
Collector peak current	$I_{C(peak)}$	40	mA
Collector power dissipation	P_C	1.5	W
Junction temperature	T_j	150	°C
Storage temperature	T_{stg}	-55 to +150	°C

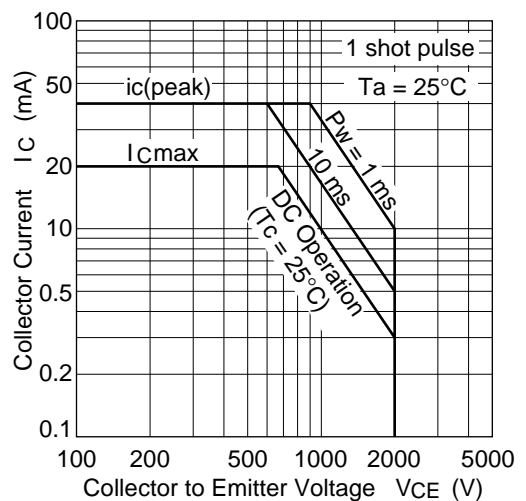
Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test conditions
Collector cutoff current	I_{CES}	—	—	500	μA	$V_{CE} = 2000\text{ V}, R_{BE} = 0$
Collector cutoff current	I_{CEO}	—	—	5	mA	$V_{CE} = 2000\text{ V}, R_{BE} = \infty$
Emitter cutoff current	I_{EBO}	—	—	500	μA	$V_{EB} = 6\text{ V}, I_C = 0$
DC current transfer ratio	h_{FE}	10	—	—		$V_{CE} = 5\text{ V}, I_C = 1\text{ mA}$
Collector to emitter saturation voltage	$V_{CE(sat)}$	—	—	5.0	V	$I_C = 10\text{ mA}, I_B = 2\text{ mA}$

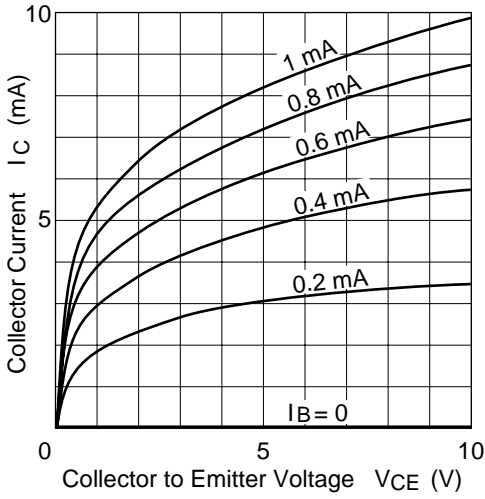
Maximum Collector Power Dissipation Curve



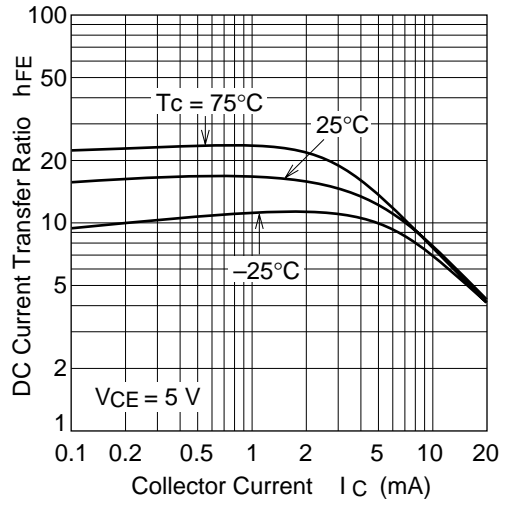
Area of Safe Operation



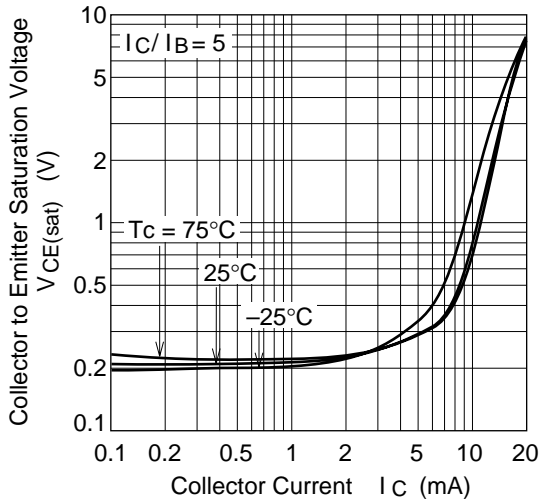
Typical Output Characteristics



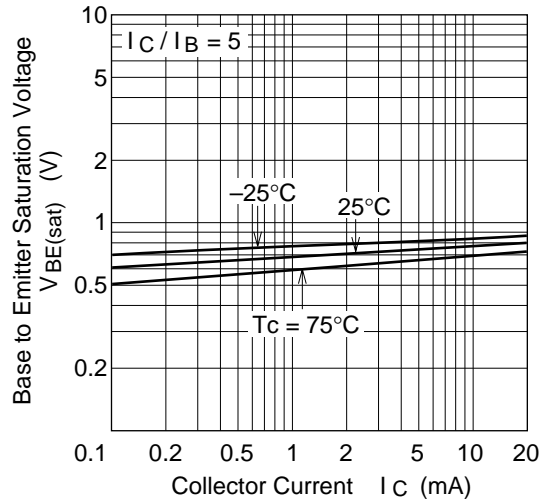
DC Current Transfer Ratio vs. Collector Current



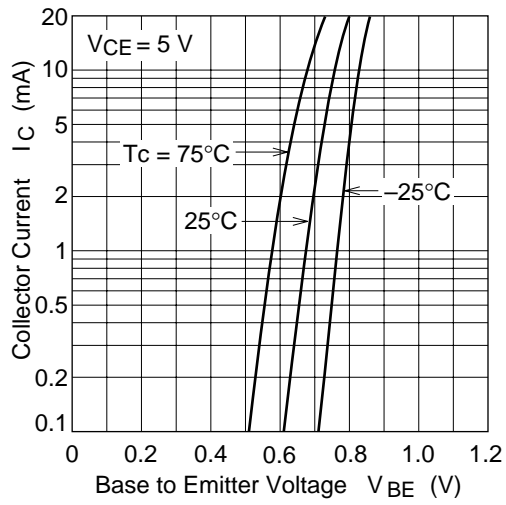
Collector to Emitter Saturation Voltage vs. Collector Current

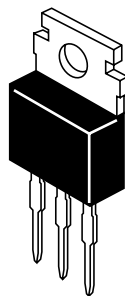
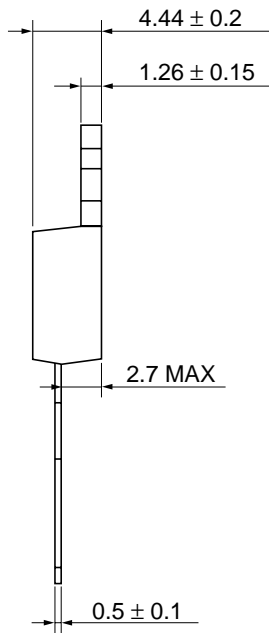


Base to Emitter Saturation Voltage vs. Collector Current



Collector Current vs. Base to Emitter Voltage





Hitachi Code	TO-220AB
JEDEC	Conforms
EIAJ	Conforms
Weight (reference value)	1.8 g

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